

# RJH60C9DPD

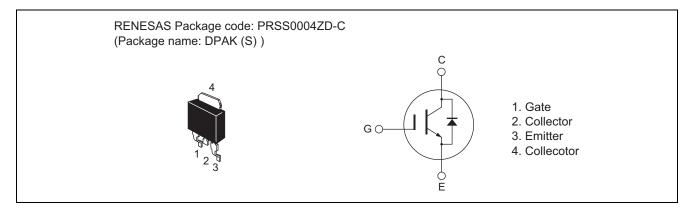
Silicon N Channel IGBT **Application: Inverter** 

REJ03G1838-0100

Rev.1.00 Oct 14, 2009

# **Features**

- High breakdown-voltage
- Low on-voltage
- Built-in diode •



# **Absolute Maximum Ratings**

				(Ta = 25°C)
Item		Symbol	Ratings	Unit
Collector to emitter voltage / diode reverse voltage		V <sub>CES</sub> / V <sub>R</sub>	600	V
Gate to emitter voltage		V <sub>GES</sub>	±30	V
Collector current	Tc = 25°C	lc	10	A
	Tc = 100°C	lc	5	A
Collector peak current		Ic(peak) <sup>Note1</sup>	20	A
Collector to emitter diode forward current		İDF	5	A
Collector to emitter diode forward peak current		i <sub>DF</sub> (peak) <sup>Note1</sup>	20	A
Collector dissipation		Pc <sup>Note2</sup>	45	W
Junction to case thermal impedance		θj-c <sup>Note2</sup>	Note2 2.78	
Junction temperature		Tj	150	°C
Storage temperature		Tstg	-55 to +150	°C
		i stg	-33 10 + 150	U

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at Tc = 25°C

 $I_F = 5 \text{ A}, \text{ di}_F/\text{dt} = 100 \text{ A}/\mu\text{s}$ 

ns

# **Electrical Characteristics**

						$(Ta = 25^{\circ}C)$	
Item	Symbol	Min	Тур	Мах	Unit	Test Conditions	
Zero gate voltage collector current / diode reverse current	I <sub>CES</sub> / I <sub>R</sub>	—	_	1.0	μA	V <sub>CE</sub> = 600 V, V <sub>GE</sub> = 0V	
Gate to emitter leak current	I <sub>GES</sub>	_	—	±100	nA	$V_{GE} = \pm 30 \text{ V}, \text{ V}_{CE} = 0 \text{ V}$	
Gate to emitter cutoff voltage	V <sub>GE(off)</sub>	4.0	6.0	8.0	V	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 1 mA	
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	1.9	2.5	V	Tc = $25^{\circ}$ C I <sub>C</sub> = 5 A, V <sub>GE</sub> = 15 V <sup>Note3</sup>	
	$V_{CE(sat)}$	—	2.0		V	Tc = $100^{\circ}$ C I <sub>C</sub> = 5 A, V <sub>GE</sub> = $15 \text{ V}^{\text{Note3}}$	
Input capacitance	Cies	—	180	—	pF	V <sub>CE</sub> = 25 V	
Output capacitance	Coes	_	19	_	pF	V <sub>GE</sub> = 0V	
Reveres transfer capacitance	Cres	—	7	—	pF	f = 1 MHz	
Total gate charge	Qg	—	8.0	—	nC	V <sub>GE</sub> = 15 V V <sub>CE</sub> = 300 V	
Gate to emitter charge	Qge	—	5.0	—	nC		
Gate to collector charge	Qgc	—	2.5	—	nC	I <sub>C</sub> = 5 A	
Switching time	t <sub>d(on)</sub>	—	25	—	ns	I <sub>C</sub> = 5 A R <sub>L</sub> = 37.5 Ω	
	tr	—	50	—	ns		
	t <sub>d(off)</sub>	_	40	—	ns	V <sub>GE</sub> = 15 V	
	t <sub>f</sub>	—	250	—	ns	Rg = 5 Ω	
FRD Forward voltage	VE		18	23	V	I <sub>F</sub> = 5 A <sup>Note3</sup>	
FRD Forward voltage	VF	—	1.8	2.3	V	$I_F = 5 A^{\text{NOIES}}$	

FRD reverse recovery time Notes: 3. Pulse test.

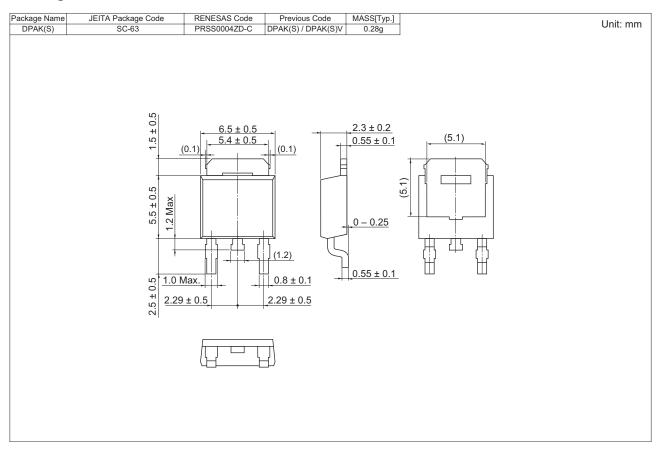
4. Under development. —

t. —The specifications potentially be changed without notice.

trr

100

# **Package Dimension**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJH60C9DPD-00-J2	3000 pcs	Taping

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